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TECHNICAL SPECIFICATION

**Nanomanufacturing - Key control characteristics -
Part 6-26: Graphene-related products - Fracture strain and stress, Young's
modulus, residual strain and residual stress: bulge test**



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CONTENTS

FOREWORD	3
INTRODUCTION	5
1 Scope	7
2 Normative references	7
3 Terms and definitions	7
3.1 General terms	7
3.2 Mechanical properties related terms	8
3.3 Key control characteristics measured according to this standard	8
3.4 Terms related to the measurement method	9
4 General	9
4.1 Measurement principle	9
4.1.1 Measurement principle of a single kind of material layer	9
4.1.2 Measurement principle of composite layer by two kinds of material	10
4.2 Sample preparation method	11
4.2.1 General	11
4.2.2 Graphene	11
4.2.3 Nanometre-thick film deposited on Si wafer	13
4.2.4 Nanometre-thick film deposited on Cu or Ni foil	14
4.3 Measurement system	16
4.4 Description of measurement equipment and apparatus	18
4.5 Supporting materials	18
5 Measurement procedure	18
5.1 Calibration of measurement equipment	18
5.2 Detailed protocol of the measurement procedure	18
6 Results to be reported	18
6.1 General	18
6.2 Product or sample identification	18
6.3 Test conditions	19
6.4 Test results	19
Annex A (informative) Format of the test report	20
Annex B (informative) Effect of sample geometry on stress-strain relation for three typical geometries	22
Annex C (informative) Worked examples	23
C.1 Graphene bulge test	23
C.2 Si_3N_4 and $\text{SiN}_x/\text{SiO}_2$ film bulge test	23
Bibliography	26
Figure 1 – Applications of mechanical properties to electrical devices	5
Figure 2 – Various measurement methods to evaluate mechanical properties of 2D and thin films	6
Figure 3 – Schematic view of the central section of sample during bulge testing	10
Figure 4 – Determination of the plane-strain modulus, the residual stress (σ_0) and residual strain (ε_0) from the experimental stress-strain curve	10
Figure 5 – Schematic view of the central section of a composite sample during bulge testing: a long rectangular membrane	10

Figure 6 – Typical steps for the preparation of a freestanding graphene (or 2D material) sample with polycarbonate (PC) supporting layer	12
Figure 7 – Typical PC/graphene samples: (a), (b) PC/graphene on SiO ₂ wafer from separate experimental runs; (c), (d) PC/graphene freestanding samples from separate experimental runs.....	12
Figure 8 – Typical steps for the preparation of a freestanding metal sample using Si wafer.....	14
Figure 9 – Typical steps for the preparation of a freestanding nanometre-thick film of graphite on metal foil substrate	15
Figure 10 – Typical freestanding samples after sample preparation process	16
Figure 11 – Measurement system consisting of bulge test chamber, pressure sensor, auto-focus light source for measuring deflection of film, high-speed camera and mass flow controller	17
Figure B.1 – Overview of three different geometries	22
Figure C.1 – Stress–strain curve from bulge test for graphene and PC/graphene	23
Figure C.2 – Bulge tests comprising both loading and unloading	24
Figure C.3 – Stress–strain curve from bulge test for SiN _X of 50 nm.....	24
Figure C.4 – Stress–strain curve from bulge test for graphite film of 50 nm.....	25
Figure C.5 – Stress–strain curve from bulge test for graphite film of 50 nm synthesized on Ni/Si wafer	25
 Table A.1 – Product identification (in accordance with the relevant blank detail specification)	20
Table A.2 – General material description	20
Table A.3 – Measurement condition.....	21
Table A.4 – Test result.....	21

INTERNATIONAL ELECTROTECHNICAL COMMISSION

Nanomanufacturing - Key control characteristics -
Part 6-26: Graphene-related products - Fracture strain and stress,
Young's modulus, residual strain and residual stress: bulge test

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Draft	Report on voting
113/924/DTS	113/939/RVDTs

Full information on the voting for its approval can be found in the report on voting indicated in the above table.

The language used for the development of this Technical Specification is English.

This document was drafted in accordance with ISO/IEC Directives, Part 2, and developed in accordance with ISO/IEC Directives, Part 1 and ISO/IEC Directives, IEC Supplement, available at www.iec.ch/members_experts/refdocs. The main document types developed by IEC are described in greater detail at www.iec.ch/publications.

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INTRODUCTION

When the characteristic dimensions of materials are reduced to the nanoscale regime, their mechanical properties exhibit significant changes compared to their bulk counterparts. These changes include enhancements in elasticity, residual strain, and fracture resistance, which are critical for reliable and high-performance nanoscale devices. Low-dimensional materials, such as graphene and nanometre-thick films, have gained widespread attention because of their exceptional thermal, optical, electrical, and mechanical properties. These unique characteristics make them indispensable in the development of advanced nanoscale technologies.

The mechanical properties of two-dimensional (2D) materials, such as Young's modulus (or elastic modulus), residual strain, residual stress, and fracture stress, are essential for their integration into diverse applications. As shown in Figure 1, these properties are utilized in several applications. These include

- strain sensors for precise mechanical deformation detection,
- energy harvesting devices using piezoelectric effects to convert mechanical to electrical energy,
- vibrational acoustic applications supporting sound generation or absorption, and
- pellicle membranes for EUV lithography that maintain structural stability under high thermal and mechanical stresses during device operation [1]¹, [2], [3], [4], [5].

These applications highlight the versatility of mechanical properties in enabling innovative engineering solutions at the nanoscale.

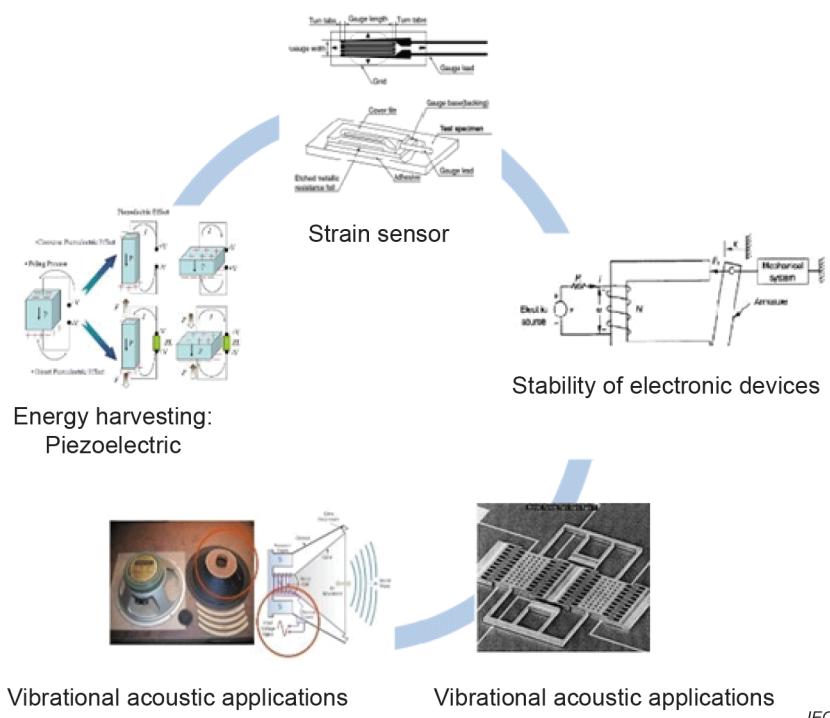


Figure 1 – Applications of mechanical properties to electrical devices

¹ Numbers in square brackets refer to the Bibliography.

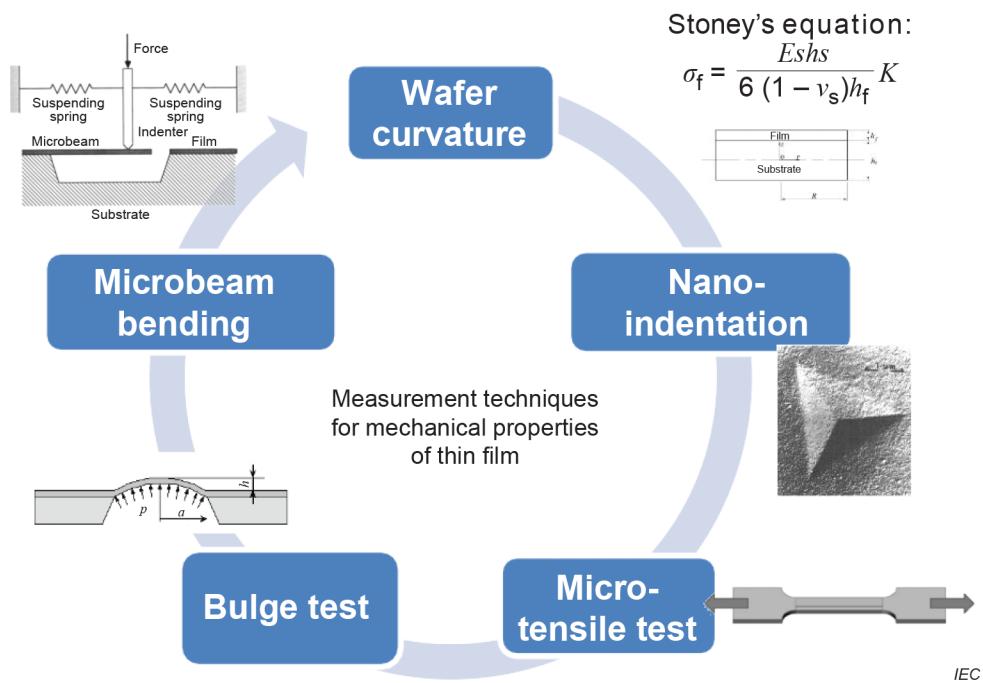


Figure 2 – Various measurement methods to evaluate mechanical properties of 2D and thin films

Accurate characterization of the mechanical properties of 2D materials and thin films is essential for their effective use in applications. However, conventional methods face significant challenges. For example, (i) substrate interference often affects techniques like nano-indentation or wafer curvature, making it difficult to isolate the intrinsic material properties, and (ii) sample preparation complexity limits the applicability of methods such as micro-tensile tests and microbeam bending. To overcome these limitations, it is important to adopt methods designed specifically for freestanding films, which can provide more accurate and reproducible results.

Figure 2 presents the various techniques used for evaluating the mechanical properties of 2D materials and thin films. These techniques include

- nano-indentation, suitable for localized measurements but limited by its focus area,
- wafer curvature, effective for measuring residual stress but influenced by the substrate,
- microbeam bending and micro-tensile tests, useful in specific cases but requiring labour-intensive preparation, and
- bulge test, a reliable method for freestanding films, which measures Young's modulus (or elastic modulus), residual strain, residual stress, and fracture stress under well-controlled conditions.

Among these, the bulge test stands out for its practicality and scalability, enabling the characterization of large areas of freestanding films without substrate interference.

1 Scope

This part of IEC TS 62607 establishes a standardized method to determine the mechanical key control characteristics (KCCs)

- Young's modulus (or elastic modulus),
- residual strain,
- residual stress, and
- fracture stress

of 2D materials and nanoscale films using the

- bulge test.

The bulge test is a reliable method where a pressure differential is applied to a freestanding film, and the resulting deformation is measured to derive the mechanical properties.

- This method is applicable to a wide range of freestanding 2D materials, such as graphene, and nanometre-thick films with thicknesses typically ranging from 1 nm to several hundred nanometres.
- This document ensures the characterization of mechanical properties essential for assessing the structural integrity and performance of materials in applications such as composite additives, flexible electronics, and energy harvesting devices.

2 Normative references

There are no normative references in this document.

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